

NPN TRANSISTORS (INCLUDING DARLINGTON)

Type	V_{CBO} V	V_{CEO} V	$I_{C(cont)}$ A	I_{CM} A	P_{tot} W	h_{FE} Min./Max. at I_C/V_{CE}		$V_{CE(sat)}$ Max. at I_C/I_B		f_T Min. MHz	Comple- ment
							mA/Volts	Volts	mA		
FZT657	300	300	0.5	1.0	2.0	50/-	100/5	0.5	100/10	30	FZT757
FZT655	150	150	1.0	2.0	2.0	50/- 20/-	500/5 1000/5	0.5 0.5	500/50 1000/200	30 30	FZT755
FZT605*	140	120	2.0	4.0	2.0	5K/- 2K/100K	500/5 1000/5	1.0 1.5	250/0.25 1000/1.0	150	FZT705*
FZT653	120	100	2.0	6.0	2.0	100/300 25/-	500/2 2000/2	0.3 0.5	1000/100 2000/200	140 140	FZT753
FZT651	80	60	3.0	6.0	2.0	80/- 40/-	1000/2 2000/2	0.3 0.6	1000/100 3000/300	140	FZT751
FZT649	35	25	3.0	8.0	2.0	100/300 15/-	1000/2 6000/2	0.3 0.6	1000/100 3000/300	150	FZT749

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							mA/Volts	Volts	mA		
FZT757	-300	-300	-0.5	-1.0	2.0	50/-	-100/-5	-0.5	-100/-10	30	FZT657
FZT755	-150	-150	-1.0	-2.0	2.0	50/- 20/-	-500/-5 -1000/-5	-0.5 -0.5	-500/-50 -1000/-200	30	FZT655
FZT705*	-140	-120	-2.0	-4.0	2.0	3K/30k 2K/-	-1000/-5 -2000/-5	-1.3 -2.5	-1000/-1.0 -2000/-2.0	100	FZT605*
FZT753	-120	-100	-2.0	-6.0	2.0	100/300 25/-	-500/-2 -2000/-2	-0.3 -0.5	-1000/-100 -2000/-200	100	FZT653
FZT751	-80	-60	-3.0	-6.0	2.0	80/- 40/-	-1000/-2 -2000/-2	-0.3 -0.6	-1000/-100 -3000/-300	100	FZT651
FZT749	-5	-25	-3.0	-8.0	2.0	100/300 15/-	-1000/-2 -6000/-2	-0.3 -0.6	-1000/-100 -3000/-300	100	FZT649

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MOSFETs

Type	BV_{DSS} V	I_D A	I_{DM} A	P_{tot} W	$V_{GS(th)}$ V at I_D			$R_{DS(on)}$ Ω at I_D			V_{GS} V	Comple- ment
					Min.	Max.	mA	Max.	A			
N-channel ZVN2106G	60	0.7	8	2	0.8	2.4	1.0	2.0	1.0	10		ZVP2106G
P-channel ZVP2106G	-60	-0.45	-4	2	-1.5	-3.5	-1.0	5.0	-0.5	-10		ZVN2106G